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# Contents

vii	<i>Authors</i>
xi	<i>Conference Committee</i>

---

## **EUV: RESIST PROCESSES: JOINT SESSION WITH CONFERENCES 10583 AND 10586**

10586 04	<b>Aqueous developers for positive tone ultrathin chemically amplified EUV resists [10586-3]</b>
10586 05	<b>EUV via hole pattern fidelity enhancement through novel resist and post-litho plasma treatment [10586-4]</b>
10586 06	<b>EUV resist sensitization and roughness improvement by PSCAR™ with in-line UV flood exposure system [10586-5]</b>

---

## **EUV: METAL-BASED RESISTS: JOINT SESSION WITH CONFERENCES 10583 AND 10586**

10586 07	<b>Surface characterization of tin-based inorganic EUV resists [10586-6]</b>
10586 08	<b>Mechanisms of photodecomposition of metal-containing EUV photoresists: isotopic labelling studies [10586-7]</b>

---

## **MATERIALS AND ETCH INTEGRATION: JOINT SESSION WITH CONFERENCES 10586 AND 10589**

10586 0A	<b>Ultimate edge-placement control using combined etch and lithography system optimizations [10586-9]</b>
----------	---

---

## **EUV: FUNDAMENTALS**

10586 0C	<b>Unraveling the role of photons and electrons upon their chemical interaction with photoresist during EUV exposure (Invited Paper) [10586-11]</b>
10586 0D	<b>Polymer effects on PAG acid yield in EUV resists [10586-12]</b>
10586 0E	<b>Characterization of metal resist for EUV lithography using infrared free electron laser [10586-13]</b>
10586 0F	<b>Investigations on EUVL metal resist dissolution behavior using in situ high speed atomic force microscopy [10586-14]</b>

---

**EUV: NOVEL PROCESSES**

---

- 10586 0G **Novel EUV resist materials for 7nm node and beyond** [10586-15]
- 10586 0H **Study of electron beam and extreme ultraviolet resist utilizing polarity change and radical crosslinking** [10586-16]
- 10586 0I **Polymer brush as adhesion promoter for EUV patterning** [10586-17]
- 10586 0J **LWR enhancement for 300mm track processing** [10586-18]
- 10586 0K **Novel Sn-based photoresist for high aspect ratio patterning** [10586-19]

---

**HARDMASKS AND UNDERLAYER**

---

- 10586 0L **The development of an SC1 removable SiARC** [10586-20]
- 10586 0M **New spin on carbon materials made from hemicellulose for hardmask layer** [10586-21]
- 10586 0N **High-carbon fullerene based spin-on organic hardmask** [10586-22]

---

**DSA MATERIALS AND CHARACTERIZATION: JOINT SESSION WITH CONFERENCES 10586 AND 10584**

---

- 10586 0P **Utilization of metal-polymer interactions for self-aligned directed self-assembly of device relevant features** [10586-24]
- 10586 0Q **Pillars fabrication by DSA lithography: material and process options** [10586-25]

---

**DSA: DEFECTIVITY AND HIGH-CHI**

---

- 10586 0U **A simulation study on bridge defects in lamellae-forming diblock copolymers** [10586-30]
- 10586 0V **Directed self-assembly of triblock copolymers for sub-10nm nanofabrication using polymeric additives** [10586-31]
- 10586 0W **Straightforward directed self-assembly process flows enabled by advanced materials** [10586-32]

---

**DSA: CYLINDER FORMING BCP AND METROLOGY**

---

- 10586 0Z **Automated lamellar block copolymer process optimization with machine learning** [10586-35]

---

**NOVEL PROCESSES**

---

- 10586 11 **Multi-color fly-cut-SAQP for reduced process variation** [10586-37]
- 10586 12 **Thick photosensitive polyimide film side wall angle variability and scum improvement for IC packaging stress control** [10586-38]
- 10586 13 **Resist-polymer ablation by mid-infrared-free-electron laser** [10586-39]
- 10586 15 **Evaluation of anti-sticking layers performances for 200mm wafer scale Smart NIL™ process through surface and defectivity characterizations** [10586-41]

---

**POSTER SESSION**

---

- 10586 16 **Application specific ratings of filters for negative-tone developer** [10586-42]
- 10586 17 **The intrinsic role of membrane morphology to reduce defectivity in advanced photochemicals** [10586-43]
- 10586 18 **Targeted removal of metallic contamination from lithography solvents using membrane purifiers** [10586-44]
- 10586 1A **Improved airborne molecular contaminant filter performance for photolithography** [10586-46]
- 10586 1D **Directed Self-Assembly (DSA) for contact applications** [10586-49]
- 10586 1E **Fast annealing DSA materials designed for sub-5 nm resolution** [10586-59]
- 10586 1F **Desirable material selection on self-aligned multi-patterning** [10586-50]
- 10586 1G **Synthesis of metal nanoparticle and patterning in polymeric films induced by electron beam** [10586-51]
- 10586 1H **Mechanism study of ion implantation on photoresist shrinkage** [10586-52]
- 10586 1I **Chemical trimming overcoat: an advanced composition and process for photoresist enhancement in lithography** [10586-58]
- 10586 1K **Development of new polyphenols applied to spin-on carbon hardmask with characteristics of high-heat resistance and good planarization** [10586-54]
- 10586 1M **Effects of fluorine contamination on spin-on dielectric thickness in semiconductor manufacturing** [10586-56]
- 10586 1N **Investigating the threshold electron energy for reactions in EUV resist materials** [10586-53]
- 10586 1O **Nanoscale inhomogeneity and photoacid generation dynamics in extreme ultraviolet resist materials** [10586-60]

10586 1P **Molecular organometallic resists for EUV (MORE): reactivity as a function of metal center (Bi, Sb, and Te) [10586-61]**

# Authors

Numbers in the index correspond to the last two digits of the seven-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first five digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Aizawa, Ryo, 06  
Amat, E., 0Q  
Araki, Mitsunori, 13  
Arceo de la Pena, Abraham, 0I  
Arisawa, You, 0M  
Asai, Masaya, 0J, 0M  
Ayothi, Ramakrishnan, 0I  
Azuma, Tsukasa, 0U  
Baranowski, Paul, 1I  
Belloni, Jacqueline, 1G  
Bernard, G., 0Z  
Biesemans, Serge, 06  
Biolsi, Peter, 1I  
Bos, S., 15  
Brainard, Robert L., 08, 0D, 1N, 1P  
Brown, Alan G., 0N  
Calderas, Eric, 0W  
Cameron, Jim, 0L  
Carcasi, Michael, 06  
Cattani, Giordano, 0A  
Cayrefourcq, Ian, 0Q, 15  
Chandonait, Jonathan, 0D, 1N  
Chang, Ching-Yu, 1D, 1O  
Chang, Vencent, 1O  
Chen, Wei-Chi, 1O  
Chen, Xuanxuan, 0V  
Cheng, Joy, 1O  
Cheng, Yuan-Chung, 1O  
Chevalier, Xavier, 0Z, 15  
Cho, Jae Kyu, 12  
Choi, Peter, 05  
Clark, Michael B., Jr., 0L  
Coley, Suzanne, 0L  
Corliss, Daniel, 0I  
Cui, Li, 0L  
Cutler, Charlotte, 0L  
Daugherty, Richard, 0W  
Dawson, Guy, 0N  
Dazai, Takahiro, 1F  
Dei, Satoshi, 06  
Delachat, F., 15  
Denbeaux, Greg H., 08, 0D, 1N, 1P  
Deng, Hai, 1E  
Dervillé, A., 0Z  
De Silva, Anuja, 0I  
De Simone, Danilo, 06, 0C  
DeVilliers, Anton, 1I  
Diulus, J. Trey, 07  
Dixit, Girish, 0A  
Dolejsi, Moshe, 0P  
Drent, Waut, 0J  
Duggan, Mark, 12  
Echigo, Masatoshi, 1K  
Enomoto, Masashi, 06  
Enomoto, Satoshi, 0H  
Fang, Zhou, 1H  
Farrell, Richard A., 1I  
Faruqui, Danish, 12  
Feldman, Leonard C., 0K  
Felix, Nelson M., 0I  
Feng, Mu, 05  
Fernandez-Regulez, M., 0Q  
Fitzgibbons, Thomas C., 0L  
Fonseca, Carlos, 05  
Foubert, Philippe, 06  
Foucher, J., 0Z  
Fournel, F., 15  
Franke, Elliott, 1I  
Frederick, Ryan T., 07  
Fujimaki, Nishiki, 0G  
Fujimori, Toru, 0G  
Fujita, Mitsuhiro, 0G  
Furukawa, Tsuyoshi, 0I  
Furutani, Hajime, 0G  
Garfunkel, Eric L., 0K  
Gharbi, A., 0Q  
Gibbons, Sean, 0D, 1N  
Goldfarb, Dario L., 04  
Greene, Daniel, 0L  
Grzeskowiak, Steven, 08, 0D, 1N, 1P  
Guerrero, Douglas, 0W  
Guo, Jing, 0I  
Gustafsson, Torgny, 0K  
Halder, Sandip, 0A  
Hamzik, James, 18  
Harumoto, Masahiko, 0J, 0M  
Hayakawa, Makoto, 06  
Hellin, David, 0A  
Herman, Gregory S., 07  
Hetzler, David, 1I  
Hoang, Brian, 1A  
Hockey, Mary Ann, 0W  
Hong, Soonsang, 1M  
Hongo, Koki, 0M  
Hori, Masafumi, 06  
Horiuchi, Junya, 1K  
Hotalen, Jodi, 1I  
Hou, Xisen, 1I

Hsieh, Ken-Hsien, 1D  
 Huang, Yuan-Chien, 1D  
 Hutchison, Danielle C., 07, 0K  
 Hwang, Sung Min, 1M  
 Ide, Hiroyuki, 06  
 Iguchi, Naoya, 16  
 Imai, Takayuki, 0E, 13  
 Itani, Toshiro, 0E, 0F  
 Ito, Kiyohito, 05  
 Jaber, Jad, 18  
 Jaenen, Patrick, 0A  
 Jee, Tae Kwon, 05  
 Kamei, Yuya, 06  
 Kaminsky, Jake, 0D, 1N  
 Kandel, Yudhishthir, 1N  
 Kasahara, Yusuke, 0U  
 Kaur, Irvinder, 1I  
 Kaushik, Kumar, 05  
 Kawada, Yukihisa, 16  
 Kawasaki, Takayasu, 0E, 13  
 Ke, Iou-Sheng, 0L  
 Kim, Hyoung-ryeun, 1M  
 Kim, Samyoung, 1M  
 Kimura, Toru, 06  
 Ko, Akitero, 1I  
 Ko, Tsung-Han, 1D  
 Koderu, Katsuyoshi, 0U  
 Kohyama, Tetsu, 17, 18  
 Koike, Kyohei, 05, 1F  
 Kondo, Yoshihiro, 06  
 Konishi, Yoshitaka, 06  
 Kozawa, Takahiro, 0H, 1G  
 Kubis, Michael, 0A  
 Kumar, Bharat, 04  
 LaBeaume, Paul, 0L  
 Lada, Tom, 0N  
 Lais, Joshua, 1A  
 Larrey, V., 15  
 Lee, Chih-Jie, 1D  
 Lee, Chung-Ju, 1D  
 Leonard, JoAnne, 0L  
 Leray, Philippe, 0A  
 Leusink, Gert, 1I  
 Li, Cui, 0L  
 Li, Jiajing, 0V  
 Li, Mengjun, 0K  
 Li, Mingqi, 1I  
 Li, Xuemiao, 1E  
 Liang, Yichen, 0W  
 Lin, Chin-Hsiang, 1D  
 Lin, John, 1O  
 Liu, Cong, 1I  
 Longenbach, Travis, 12  
 Luca, Melissa, 0A  
 Ly, Saksatha, 18  
 Lyubinetzky, Igor, 07  
 Machida, Kohei, 0H  
 Makinoshima, Takashi, 1K  
 Manichev, Viacheslav, 0K  
 Marignier, Jean-Louis, 1G  
 Maruyama, Ken, 06  
 Maslow, Mark, 05  
 Masuda, Kazushi, 16  
 McClelland, Alexandra, 0N  
 Mehta, Sohan Singh, 12  
 Meli, Luciana, 0I  
 Meliorisz, Balint, 06  
 Melvin, Lawrence S., III, 1N  
 Metzler, Dominik, 0I  
 Mignot, Yann, 0I  
 Minekawa, Yukie, 06  
 Mirza, Fahad, 12  
 Miura, Kozue, 17  
 Miyagi, Ken, 0U  
 Miyake, Masayuki, 06  
 Mikhlespour, Salman, 0A  
 Montgomery, Warren, 0N  
 Morgan, Justin, 12  
 Morikita, Shinya, 05  
 Morita, Kazuyo, 0M  
 Moriya, Teruhiko, 06  
 Mosfavi, Mehran, 1G  
 Murakami, Tetsuya, 16  
 Murphy, Michael, 08, 0D, 1P  
 Nafus, Kathleen, 06  
 Nagahara, Seiji, 06  
 Nagai, Tomoki, 06  
 Nakagawa, Hisashi, 06  
 Nakashima, Hideo, 06  
 Nakayama, Chisayo, 0J, 0M  
 Naruoka, Takehiko, 06  
 Navarro, Christophe, 0Q, 15  
 Nealey, Paul, 0P, 0V  
 Nicolet, Céilia, 0Q, 15  
 Nihashi, Wataru, 0G  
 Nyman, May, 07, 0K  
 Oh, Changyeol, 1M  
 Ohmori, Katsumi, 1F  
 Ohyashiki, Yasushi, 17  
 Oka, Hironori, 0G  
 Olsen, Morgan R., 07  
 Omatsu, Tadashi, 0G  
 O'Meara, David, 1I  
 Ongayi, Owendi, 0L  
 Oshima, Akihiro, 06  
 Pain, L., 0Q  
 Park, Jong, 1I  
 Peng, Yu, 1E  
 Perego, M., 0Q  
 Perez-Murano, F., 0Q  
 Petersen, John S., 06, 0C  
 Peterson, Brennan, 0A  
 Phillippe, J.-C., 15  
 Pieczulewski, Charles, 0J  
 Pimenta-Barros, P., 0Q  
 Pollentier, Ivan, 0C  
 Popere, Bhooshan, 0L  
 Premachandran, C. S., 12  
 Rabie, Mohamed, 12  
 Raley, Angelique, 1I



Raman, Thiagarajan, 12  
 Rathore, Ashish, 0C  
 Reidy, Sean, 12  
 Reijnen, Liesbeth, 05  
 Reynaud, G., 0Q  
 Rincon-Delgado, Paulina, 0V  
 Robinson, Alex P. G., 0N  
 Rowell, Kevin, 1I  
 Rutigliani, Vito, 0A  
 Sakita, Kyohei, 0G  
 Santillan, Julius Joseph, 0E, 0F  
 Saouaf, O., 0Q  
 Sato, Hironobu, 0U  
 Sato, Takashi, 1K  
 Schoofs, Stijn, 05  
 Seino, Yuriko, 0U  
 Seshadri, Indira, 0I  
 Seshimo, Takehiro, 1F  
 Shamma, Nader, 0A  
 Shen, Han-Ping, 1D  
 Shi, Heguang, 1H  
 Shima, Motoyuki, 06  
 Shimada, Ryo, 06  
 Shimizu, Yoko, 1K  
 Shiozawa, Takahiro, 06  
 Shiraiishi, Gosuke, 06  
 Shiraiishi, Masayuki, 0U  
 Shirakawa, Michihiro, 0G  
 Singh, Lovejeet, 0I  
 Sitterly, Jacob, 08, 1P  
 Sobieski, Daniel, 0A  
 Soedibyo, Rio A., 12  
 Spence, Chris, 05  
 Stock, Hans-Jürgen, 06  
 Stokes, Harold, 0J, 0M  
 Sullivan, Chris, 0L  
 Tagawa, Seiichi, 06, 1G  
 Takeshita, Kazuhiro, 06  
 Takigawa, Tomoaki, 1K  
 Tanaka, Yuji, 0J, 0M  
 Tapily, Kanda, 1I  
 Teyssèdre, H., 15  
 Timoshkov, Vadim, 05  
 Tiron, R., 0Q  
 Tomono, Masaru, 06  
 Toriumi, Minoru, 0E, 13  
 Tsuchihashi, Toru, 0G  
 Tsukiyama, Koichi, 0E, 13  
 Tsuzuki, Shuichi, 16  
 Umeda, Toru, 16  
 Vandenberghe, Geert, 06, 0C  
 Vandereyken, Jelle, 0J  
 van der Straten, Koen, 0A  
 Vanelderren, Pieter, 0C  
 Vesters, Yannick, 0C  
 Viantka, Katja, 0A  
 Wajda, Cory, 1I  
 Wang, Chien-Wei, 1O  
 Wang, Yu-Fu, 1O  
 Weineck, Gerald, 1A  
 Welling, Ulrich, 1N  
 Weng, Ming-Hui, 1D  
 Wise, Rich, 0A  
 Wong, Sabrina, 0L  
 Wu, Aiwen, 17, 18  
 Wu, Cheng-Han, 1D  
 Wu, Chieh-Han, 1D  
 Wu, Ping-Jui, 1O  
 Xu, Cheng Bai, 1I  
 Xu, Kui, 0W  
 Xu, Yongan, 0I  
 Yaegashi, Hidetami, 05, 1F  
 Yamada, Kazuki, 1F  
 Yamada, Shintaro, 0L  
 Yamamoto, Hiroki, 1G  
 Yamamoto, Kimiko, 0M  
 Yamashita, Fumiko, 05  
 Yamato, Masatoshi, 1F  
 Yang, Dongxu, 1H  
 Yeung, Marco, 12  
 Yoshida, Keisuke, 06  
 Yoshihara, Kosuke, 06  
 Yoshimura, Shota, 05  
 Yoshino, Takumi, 0H  
 Yu, Fangzhou, 0K  
 Zhou, Chun, 0V  
 Zhou, Jianuo, 1E



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- 1 Keynote Session  
**Christoph K. Hohle**, Fraunhofer-Institut für Photonische Mikrosysteme (Germany)  
**Roel Gronheid**, KLA-Tencor/ ICOS Belgium (Belgium)
- 2 EUV: Resist Processes: Joint session with conferences 10583 and 10586  
**Thomas I. Wallow**, ASML Brion Technologies (United States)  
**James W. Thackeray**, Dow Electronic Materials (United States)
- 3 EUV: Metal-based Resists: Joint session with conferences 10583 and 10586  
**Jason K. Stowers**, Inpria Corporation (United States)  
**Christopher S. Ngai**, Applied Materials, Inc. (United States)
- 4 Materials and Etch Integration: Joint session with conferences 10586 and 10589  
**Qinghuang Lin**, IBM Thomas J. Watson Research Center (United States)  
**Sebastian U. Engelmann**, IBM Thomas J. Watson Research Center (United States)
- 5 EUV: Fundamentals  
**Clifford L. Henderson**, University of South Florida (United States)  
**Craig D. Higgins**, GLOBALFOUNDRIES Inc. (United States)
- 6 EUV: Novel Processes  
**Danilo De Simone**, IMEC (Belgium)  
**Rick Uchida**, Tokyo Ohka Kogyo America, Inc. (United States)
- 7 Hardmasks and Underlayer  
**Douglas J. Guerrero**, Brewer Science, Inc. (Belgium)  
**Ryan Callahan**, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
- 8 DSA Materials and Characterization: Joint session with conferences 10586 and 10584  
**Ralph R. Dammel**, EMD Performance Materials Corporation (United States)  
**Chi-Chun Liu**, IBM Corporation (United States)

- 9 DSA Materials and Integration: Joint session with conferences 10586 and 10584  
**Daniel Sanders**, IBM Research - Almaden (United States)  
**J. Alexander Liddle**, National Institute of Standards and Technology (United States)
- 10 DSA: Defectivity and High-chi  
**Mark H. Somervell**, Tokyo Electron America, Inc. (United States)  
**Ralph R. Dammel**, EMD Performance Materials Corporation (United States)
- 11 DSA: Cylinder Forming BCP and Metrology  
**Ramakrishnan Ayothi**, JSR Micro, Inc. (United States)  
**Raluca Tiron**, CEA-LETI (France)
- 12 Novel Processes  
**Gilles R. Amblard**, SAMSUNG Austin Semiconductor LLC (United States)  
**Nobuyuki N. Matsuzawa**, Panasonic Corporation (Japan)

